

# APTDF60H601G

# Fast Diode Full Bridge Power Module

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9 10

CR3

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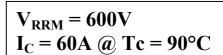
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CR1

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#### Application

- Uninterruptible Power Supply (UPS)
- Induction heating
- Welding equipment
- High speed rectifiers

#### Features

- Ultra fast recovery times
- Soft recovery characteristics
- High blocking voltage
- High current
- Low leakage current
- Very low stray inductance
- High level of integration

#### Benefits

- Outstanding performance at high frequency operation
- Low losses
- Low noise switching
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- RoHS Compliant
- All multiple inputs and outputs must be shorted together 3/4; 5/6; 7/8; 1/2; 9/10

### Absolute maximum ratings

| Symbol                                 | Parameter                       |                    |         | Max ratings         | Unit |   |
|--|---------------------------------|--------------------|---------|---------------------|------|---|
| V <sub>R</sub>                         | Maximum DC reverse Voltage      |                    |         | 600                 | V    |   |
| V <sub>RRM</sub>                       | Maximum Peak Repetitive Revers  | ve Reverse Voltage |         |                     | 600  | v |
| т                                      | Maximum Average Forward         | Destru sevel       | 500/    | $T_C = 25^{\circ}C$ | 92   |   |
| $\mathbf{I}_{\mathrm{F}(\mathrm{AV})}$ | Current                         | Duty cycl          | e = 50% | $T_C = 90^{\circ}C$ | 60   | А |
| I <sub>FSM</sub>                       | Non-Repetitive Forward Surge Cu | rrent 8.3ms        |         | $T_J = 45^{\circ}C$ | 500  |   |

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



## All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

# **Electrical Characteristics**

| Symbol          | Characteristic                  | Test Conditions                              | Min                    | Тур | Max | Unit |    |
|-----------------|---------------------------------|--|------------------------|-----|-----|------|----|
| $V_{\rm F}$     |                                 | $I_F = 60A$                                  |                        |     | 1.7 | 2.3  |    |
|                 | Diode Forward Voltage           | $I_{\rm F} = 120 {\rm A}$                    |                        |     | 2   |      | V  |
|                 |                                 | $I_F = 60A$                                  | $T_{j} = 125^{\circ}C$ |     | 1.4 |      |    |
| т               | Maximum Reverse Leakage Current | $V_{\rm R} = 600 V$ $T_{\rm i} = 25^{\circ}$ | $T_i = 25^{\circ}C$    |     |     | 25   |    |
| I <sub>RM</sub> | Maximum Reverse Leakage Current | $\mathbf{v}_{\mathrm{R}} = 000  \mathbf{v}$  | $T_{j} = 125^{\circ}C$ |     |     | 500  | μA |
| CT              | Junction Capacitance            | $V_R = 200V$                                 |                        |     | 145 |      | pF |

### **Dynamic Characteristics**

| Symbol           | Characteristic           | Test Conditions                                      |                        | Min | Тур  | Max | Unit |
|------------------|--------------------------|--|------------------------|-----|------|-----|------|
| t <sub>rr</sub>  | Reverse Recovery Time    | $I_{\rm F} = 60 \text{A}$ $V_{\rm R} = 400 \text{V}$ | $T_j = 25^{\circ}C$    |     | 70   |     | - ns |
| ι <sub>rr</sub>  | Reverse Recovery Time    |  | $T_{j} = 125^{\circ}C$ |     | 140  |     |      |
| Q <sub>rr</sub>  | Reverse Recovery Charge  |  | $T_j = 25^{\circ}C$    |     | 100  |     | nC   |
| Zrr              | Reverse Receivery Charge | $di/dt = 200 A/\mu s$                                | $T_1 = 125^{\circ}C$   |     | 690  |     | пе   |
| I <sub>RRM</sub> |                          |  | $T_j = 25^{\circ}C$    |     | 4    |     | А    |
| IRRM             |                          |  | $T_{j} = 125^{\circ}C$ |     | 9    |     |      |
| t <sub>rr</sub>  | Reverse Recovery Time    | $I_F = 60A$<br>$V_R = 400V$<br>$di/dt = 1000A/\mu s$ |                        |     | 80   |     | ns   |
| Q <sub>rr</sub>  | Reverse Recovery Charge  |  | $T_j = 125^{\circ}C$   |     | 1540 |     | nC   |
| I <sub>RRM</sub> | Reverse Recovery Current |  |                        |     | 31   |     | Α    |

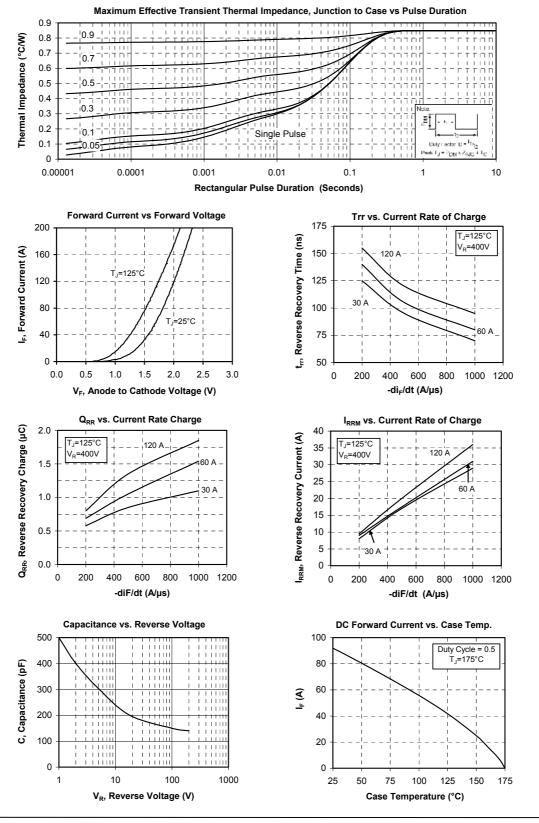
## Thermal and package characteristics

| Symbol            | Characteristic  |             |    | Min  | Тур | Max  | Unit |
|-------------------|---|-------------|----|------|-----|------|------|
| $R_{thJC}$        | Junction to Case Thermal Resistance                           |             |    |      |     | 0.85 | °C/W |
| V <sub>ISOL</sub> | RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz |             |    | 4000 |     |      | V    |
| TJ                | Operating junction temperature range                          |             |    | -40  |     | 175  |      |
| T <sub>STG</sub>  | Storage Temperature Range                                     |             |    | -40  |     | 125  | °C   |
| T <sub>C</sub>    | Operating Case Temperature                                    |             |    | -40  |     | 100  |      |
| Torque            | Mounting torque   | To heatsink | M4 | 2    |     | 3    | N.m  |
| Wt                | Package Weight  |             |    |      |     | 80   | g    |



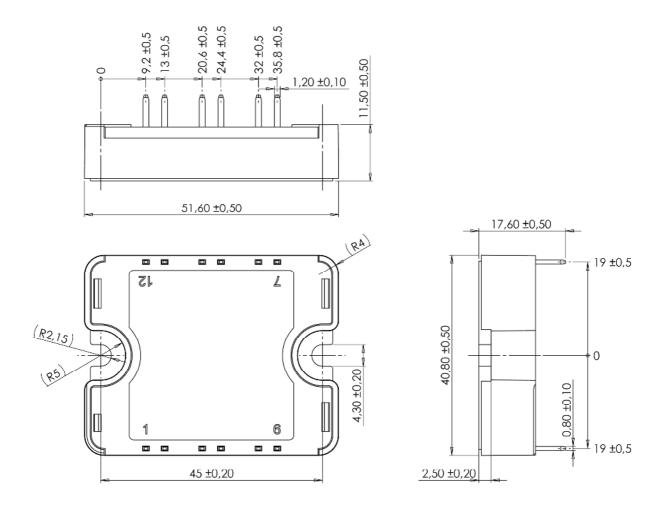
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#### **Typical Performance Curve**





### SP1 Package outline (dimensions in mm)



See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com



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